

# **SANYO Semiconductors**

# DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

# ECH8309 — General-Purpose Switching Device Applications

#### **Features**

- 1.8V drive
- · Halogen free compliance
- · Protection diode in

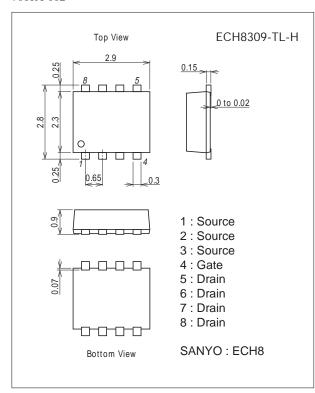
#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-9.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-40	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7011A-002



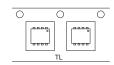
#### **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

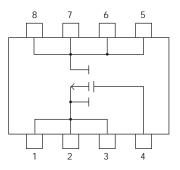
#### Packing Type: TL



#### Marking



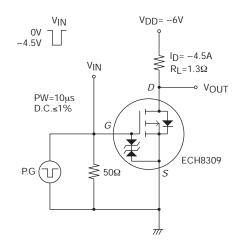
#### **Electrical Connection**



#### Electrical Characteristics at Ta=25°C

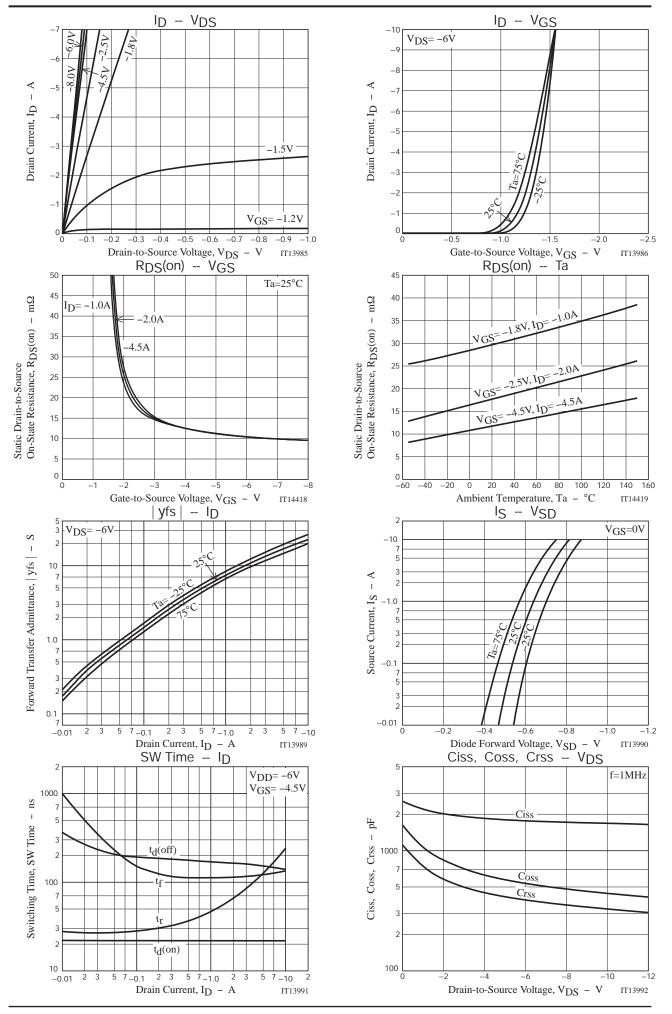
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Onit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V <sub>D</sub> S=-6V, I <sub>D</sub> =-4.5A	9.6	16		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-4.5A, V <sub>G</sub> S=-4.5V		12	16	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-2A, V <sub>G</sub> S=-2.5V		18	26	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-1A, V <sub>G</sub> S=-1.8V		30	53	mΩ	
Input Capacitance	Ciss			1780		pF	
Output Capacitance	Coss	V <sub>DS</sub> =-6V, f=1MHz		540		pF	
Reverse Transfer Capacitance	Crss			390		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			22		ns	
Rise Time	t <sub>r</sub>	Considered Took Classifi		110		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		157		ns	
Fall Time	tf			123		ns	
Total Gate Charge	Qg			18		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-6V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-9.5A		2.8		nC	
Gate-to-Drain "Miller" Charge	Qgd	]		4.9		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-9.5A, V <sub>GS</sub> =0V		-0.8	-1.2	V	

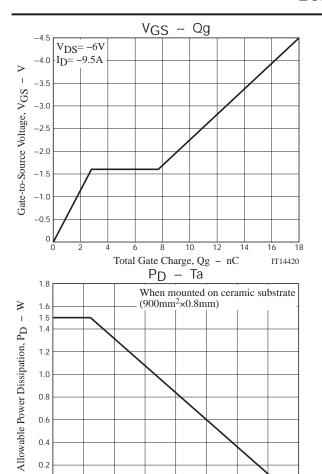
## Switching Time Test Circuit



## **Ordering Information**

Device Package		Shipping	memo	
ECH8309-TL-H	CH8309-TL-H ECH8		Pb Free and Halogen Free	





40 60 80 100 120 Ambient Temperature, Ta – °C

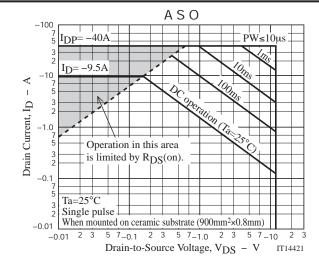
140

160 IT14422

0

0

20

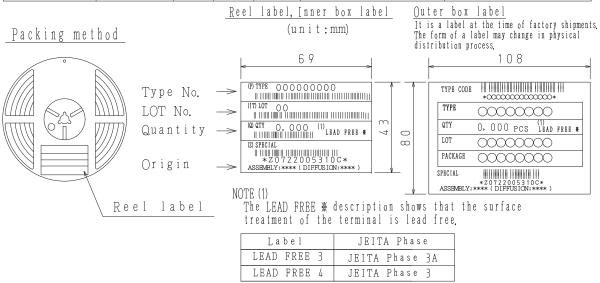


#### **Embossed Taping Specification**

#### ECH8309-TL-H

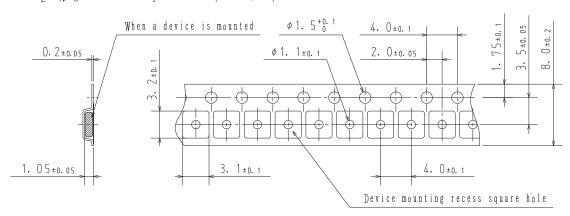
#### 1. Packing Format

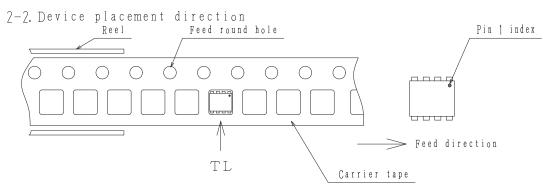
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	ing format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)		
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



#### 2. Taping configuration

2-1. Carrier tape size (unit:mm)





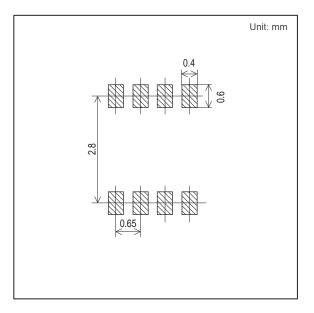
Those with pin 1 index on the feed hole side · · · · · TL

# **Outline Drawing**

ECH8309-TL-H

# Mass (g) Unit 0.02 \* For reference mm 0. 15<sup>+0. 1</sup><sub>-0. 05</sub> 0. 25±0.06 2. 9±0.06 0~0.02 2. 8±0. 05 2. 3±0.06 LOT No. 0. 25±0.06 0. 3<sup>+0. 1</sup> 0.65 PIN#1 0. 9±0. 05 0.05 \$ \$

## Land Pattern Example



Note on usage: Since the ECH8309 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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